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# FQN1N50C N-Channel QFET<sup>®</sup> MOSFET

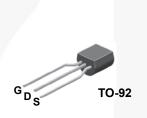
# 500 V, 0.38 A, 6 $\Omega$

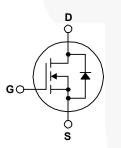
### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

## Features

- 0.38 A, 500 V,  $R_{DS(on)}$  = 6  $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 0.19 A
- Low Gate Charge (Typ. 4.9 nC)
- Low Crss (Typ. 4.1 pF)
- 100% Avalanche Tested





## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter			FQN1N50CTA	Unit	
V <sub>DSS</sub>	Drain-Source Voltage		500		V	
ID	Drain Current	- Continuous (T <sub>C</sub> = 25°C)		0.38	A	
		- Continuous (T <sub>C</sub> = 100°C)		0.24	A	
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)		(Note 1)	3.04	A	
V <sub>GSS</sub>	Gate-Source Voltage			± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		(Note 2)	44.4	mJ	
I <sub>AR</sub>	Avalanche Current		(Note 1)	0.38	А	
E <sub>AR</sub>	Repetitive Avalanche Energy		(Note 1)	0.21	mJ	
dv/dt	Peak Diode Recovery dv/dt (N		(Note 3)	4.5	V/ns	
P <sub>D</sub>	Power Dissipation ( $T_A = 25^{\circ}C$ )			0.89	W	
	Power Dissipation (T <sub>L</sub> = 25°C)			2.08	W	
	- Derate above 25°C			0.017	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.			300	°C	

# Thermal Characteristics

Symbol	Parameter		FQN1N50CTA	Unit
$R_{\theta JL}$	Thermal Resistance, Junction-to-Lead, Max.	(Note 5a)	60	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction-to-Ambient, Max.	(Note 5b)	140	·C/W

December 2013

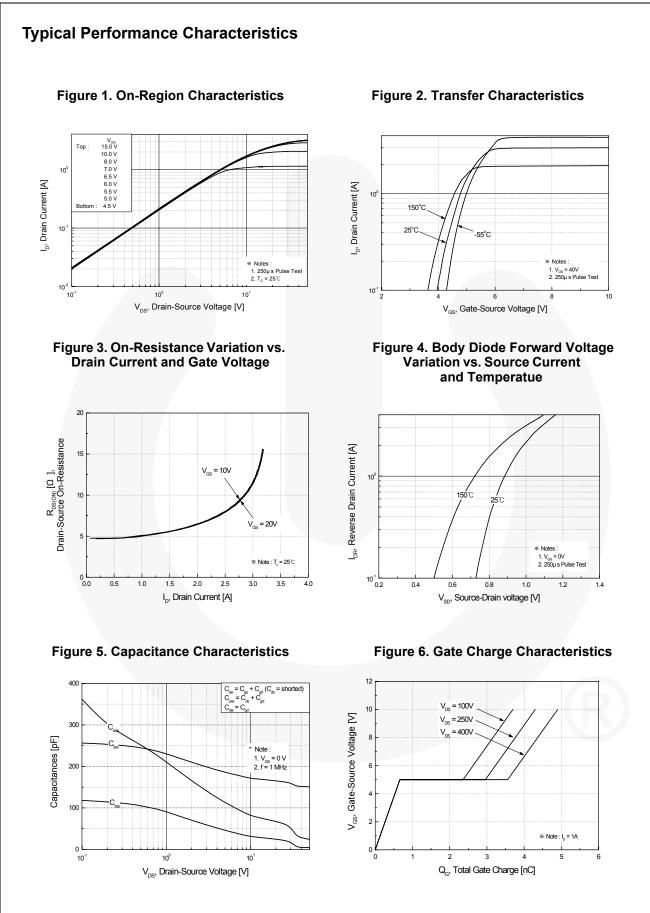
Part Number		Top Mark	Package	ckage Packing Method Reel		Size	Tape W	'idth	Quantity	
FQN1N	I50CTA	1N50C	TO-92	TO-92 AMMO N		A	N/A		2000 units	
Electric	al Char	racteristics T <sub>c</sub> = 25°C	unless otherwi	se noted.						
Symbol		Parameter		Test Conditions		Min.	Тур.	Max.	Unit	
Off Charac	teristics									
BV <sub>DSS</sub>	Drain-S	ource Breakdown Voltage	$V_{GS}$	= 0 V, I <sub>D</sub> = 250 μA		500			V	
ΔΒV <sub>DSS</sub> / ΔΤ <sub>J</sub>	Breakdo Coeffici	own Voltage Temperature ent	I <sub>D</sub> = 1	$I_D = 250 \ \mu$ A, Referenced to 25°C			0.5		V/°C	
I <sub>DSS</sub>	Zero Ga	ate Voltage Drain Current	$V_{DS}$	= 500 V, V <sub>GS</sub> = 0 V				50	μA	
			$V_{DS}$	= 400 V, T <sub>C</sub> = 125°C				250	μA	
I <sub>GSSF</sub>	Gate-Bo	ody Leakage Current, Forwa	ard V <sub>GS</sub>	= 30 V, V <sub>DS</sub> = 0 V				100	nA	
I <sub>GSSR</sub>	Gate-Bo	ody Leakage Current, Reve	se V <sub>GS</sub>	= -30 V, V <sub>DS</sub> = 0 V				-100	nA	
On Charac	teristics									
V <sub>GS(th)</sub>	Gate Th	nreshold Voltage	$V_{\text{DS}}$	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA		2.0		4.0	V	
R <sub>DS(on)</sub>	Static D On-Res	rain-Source istance	V <sub>GS</sub>	= 10 V, I <sub>D</sub> = 0.19 A		-	4.6	6.0	Ω	
9 <sub>FS</sub>	Forward	d Transconductance	$V_{DS}$	= 40 V, I <sub>D</sub> = 0.19A		\	0.6		S	
Dynamic C	haracteristi	ics								
C <sub>iss</sub>	Input Ca	apacitance		= 25 V, V <sub>GS</sub> = 0 V,			150	195	pF	
C <sub>oss</sub>	Output	Capacitance	f = 1	f = 1.0 MHz			28	40	pF	
C <sub>rss</sub>	Reverse	e Transfer Capacitance					4.1		pF	
Switching	Characteris	tics								
t <sub>d(on)</sub>	Turn-Or	n Delay Time		$V_{DD} = 250 \text{ V}, \text{ I}_{D} = 1.0 \text{ A},$ $R_{G} = 25 \Omega$			10	30	ns	
r	Turn-Or	n Rise Time	R <sub>G</sub> =				10	30	ns	
t <sub>d(off)</sub>	Turn-Of	f Delay Time					20	50	ns	
f	Turn-Of	f Fall Time			(Note 4)		15	40	ns	
Qg	Total Ga	ate Charge	20	$V_{DS} = 400 \text{ V}, \text{ I}_{D} = 1.0 \text{ A},$ $V_{GS} = 10 \text{ V}$			4.9	6.4	nC	
Q <sub>gs</sub>	Gate-Se	ource Charge	V <sub>GS</sub>				0.66		nC	
Q <sub>gd</sub>	Gate-D	rain Charge			(Note 4)		2.9		nC	
Drain-Sour	ce Diode C	haracteristics and Maximu	m Ratings							
s	Maximu	m Continuous Drain-Source	e Diode Forw	vard Current				0.38	А	
SM	Maximu	im Pulsed Drain-Source Dio		orward Current				3.04	А	
V <sub>SD</sub>	Drain-S	ource Diode Forward Voltag		$V_{GS}$ = 0 V, I <sub>S</sub> = 0.38 A				1.4	V	
t <sub>rr</sub>	Reverse	e Recovery Time		= 0 V, I <sub>S</sub> = 1.0 A,		-	188		ns	
Q <sub>rr</sub>	Reverse	e Recovery Charge	ai <sub>F</sub> /	dt = 100 A/µs			0.55		μC	

2. L = 80 mH, I\_{AS} = 1.0 A, V\_{DD} = 50 V, R\_G = 25  $\Omega,$  starting  $\mbox{ T}_{J}$  = 25°C.

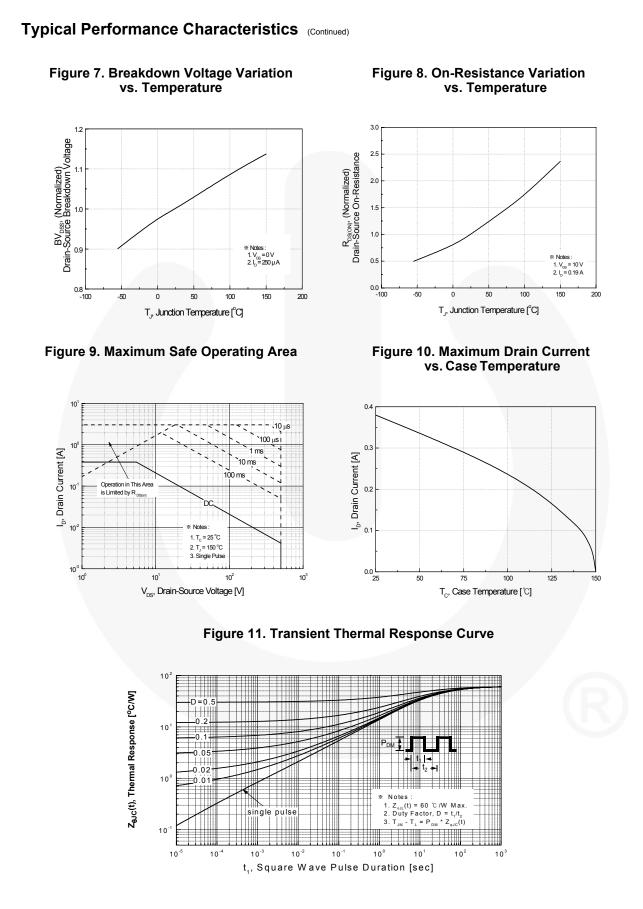
3. I\_{SD} \leq 0.38 A, di/dt  $\leq 200$  A/µs, V\_{DD}  $\leq BV_{DSS,}$  starting T\_J = 25°C.

4. Essentially independent of operating temperature.

FQN1N50C — N-Channel QFET® MOSFET



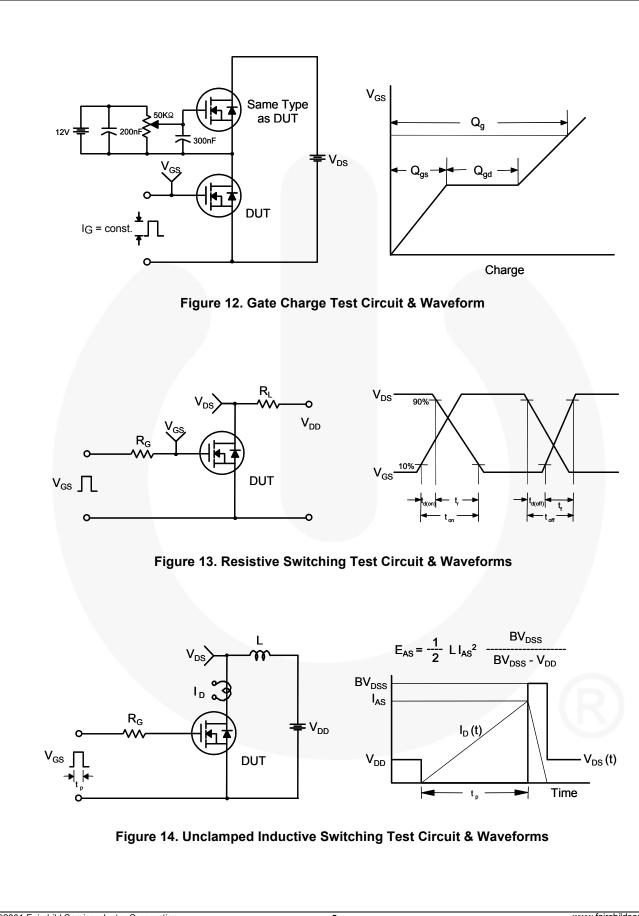
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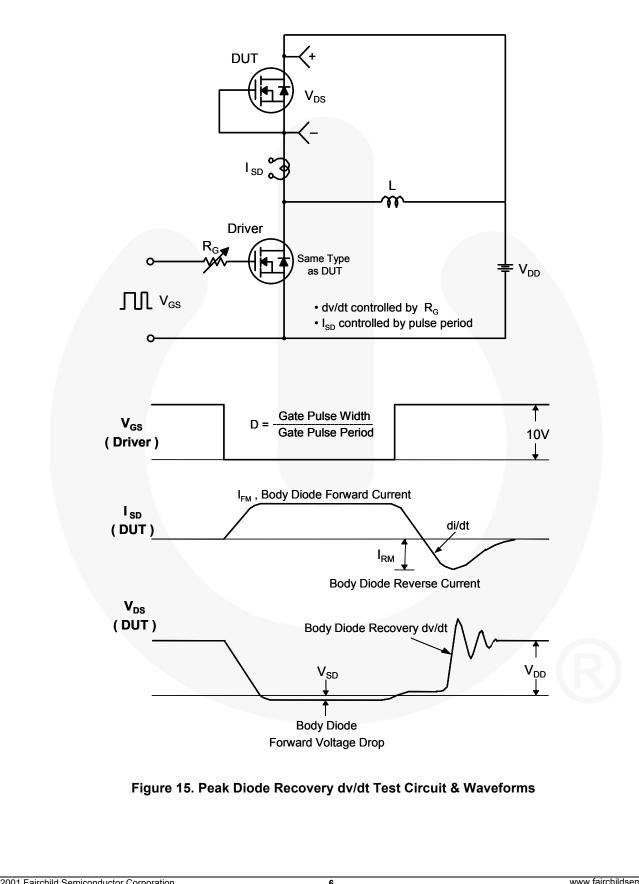
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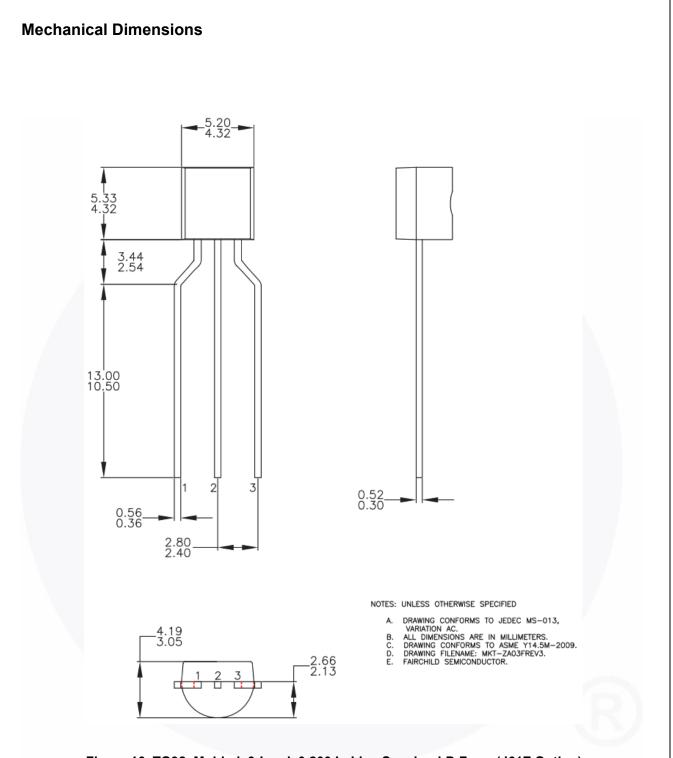
4

FQN1N50C — N-Channel QFET<sup>®</sup> MOSFET



FQN1N50C — N-Channel QFET® MOSFET





### Figure 16. TO92, Molded, 3-Lead, 0.200 In Line Spacing LD Form (J61Z Option)

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